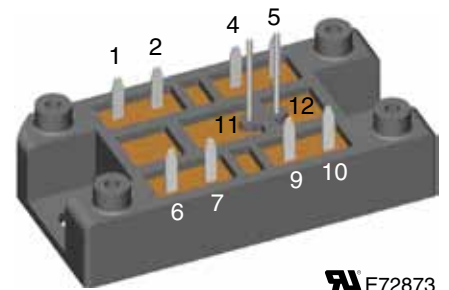
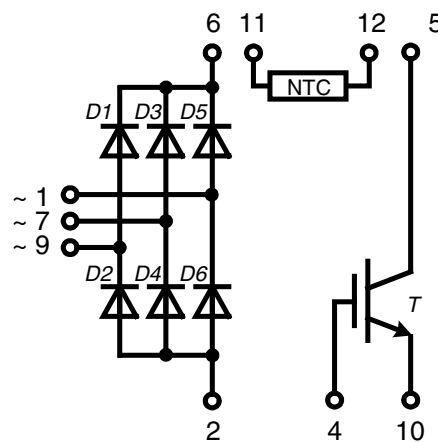


Three Phase Rectifier Bridge with Brake IGBT

$V_{RRM} = 1600\text{ V}$
 $I_{dAVM} = 110\text{ A}$

Part name (Marking on product)

VUI72-16NOXT



Features:

- Three phase mains rectifier
- Brake IGBT with low saturation voltage

Application:

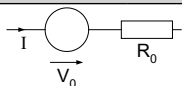
- Drives with
 - mains input
 - DC link
 - inverter or chopper feeding the machine
 - motor and generator/brake operation

Package:

- High level of integration
- Solder terminals for PCB mounting
- UL registered E72873
- Isolated DCB ceramic base plate
- Large creepage and strike distances
- High reliability

Chopper IGBT T

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$			1200	V
V_{GES}	max. DC gate voltage	continuous	-20		+20	V
I_{C25}	collector current	DC			58	A
I_{C80}		DC			40	A
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 35\text{ A}; V_{GE} = 15\text{ V}$			1.85 2.15	V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 1\text{ mA}$	5.4		6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$			0.1	mA mA
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			500	nA
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 35\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 27\ \Omega; L = 100\ \mu\text{H}$			70	ns
t_r	current rise time				40	ns
$t_{d(off)}$	turn-off delay time				250	ns
t_f	current fall time				100	ns
E_{on}	turn-on energy per pulse				3.8	mJ
E_{off}	turn-off energy per pulse				4.1	mJ
Q_{Gon}		$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 35\text{ A}$			110	nC
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 27\ \Omega; L = 100\ \mu\text{H}$			70	A
V_{CEK}		clamped inductive load; $T_{VJ} = 125^{\circ}\text{C}$			$\leq V_{CES} - L_S \cdot d_i/dt$	V
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 27\ \Omega; \text{non-repetitive}$			10	μs
R_{thJC}	thermal resistance junction to case				0.65	K/W
R_{thJH}	thermal resistance case to heatsink	with heat transfer paste, see mounting instructions			0.9	K/W

Equivalent Circuits for Simulation


Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_0	Diode	D1 - D6			0.85	V
R_0					7	$\text{m}\Omega$
V_0	IGBT	T			1.1	V
R_0					40	$\text{m}\Omega$

Input Rectifier Diode D1 - D6

Symbol	Conditions	Ratings			Unit	
		min.	typ.	max.		
V_{RRM}	max. repetitive reverse voltage			1600	V	
I_{FAV}	average forward current	sine 180°		40	A	
$I_{D(AV)M}$	max. average DC output current	rectangular; $d = 1/3$; bridge		110	A	
I_{FSM}	max. surge forward current	$t = 10$ ms; sine 50 Hz		530	A	
P_{tot}	total power dissipation			100	W	
I_R	reverse current	$V_R = V_{RRM}$		0.02	mA	
		$V_R = 0.8 \cdot V_{RRM}$		0.4	mA	
V_F	forward voltage	$I_F = 25$ A	$T_{VJ} = 25^\circ\text{C}$	1.0	1.1	V
			$T_{VJ} = 125^\circ\text{C}$	0.9		V
R_{thJC}	thermal resistance junction to case	per diode		1.2	K/W	
R_{thJH}	thermal resistance case to heatsink	with heat transfer paste		1.42	K/W	

Temperature Sensor NTC

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
R_{25}	resistance	$\left\{ R(T) = R_{25} \cdot e^{B_{25/100} \left[\frac{1}{T} - \frac{1}{298K} \right]} \right\}$	$T = 25^\circ\text{C}$	2.2		k Ω
$B_{25/100}$				3560		K

Module

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
I_{RMS}	RMS current	per pin			100	A
T_{VJ}	operating temperature		-40		150	°C
T_{VJM}	max. virtual junction temperature				150	°C
T_{stg}	storage temperature		-40		125	°C
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1$ mA; 50/60 Hz;			3600	V~
M_d	mounting torque	(M5)	2		2.5	Nm
d_S	creep distance on surface		5			mm
d_A	strike distance through air		5			mm
Weight				35		g

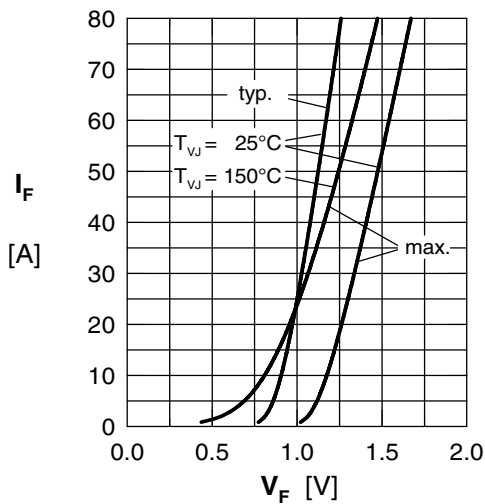


Fig. 1 Forward current vs. voltage drop per rectifier diode

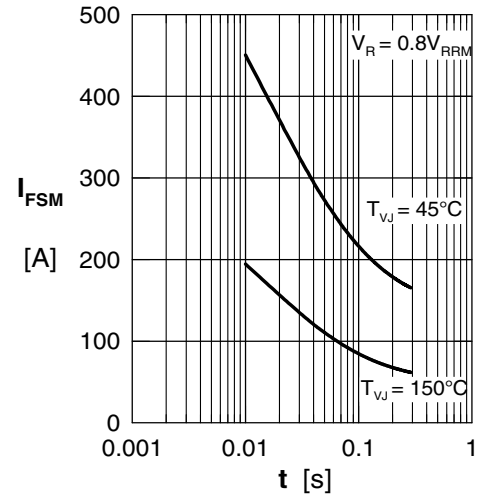


Fig. 2 Surge overload current per rectifier diode

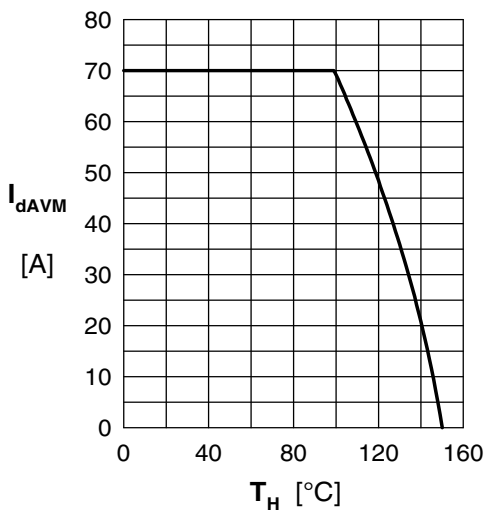


Fig. 3 Max. forward current vs. heatsink temperature (Rectifier bridge)

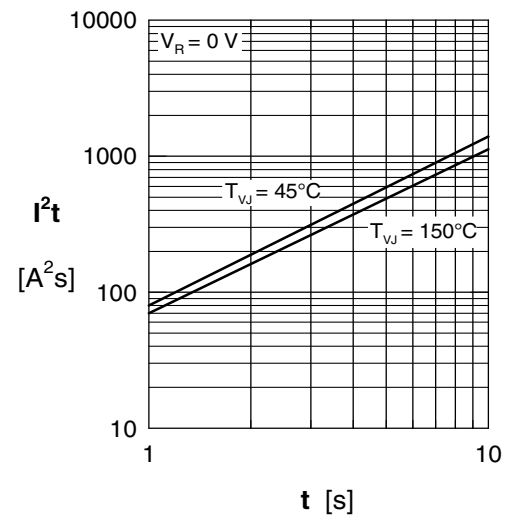


Fig. 4 I^2t versus time per rectifier diode

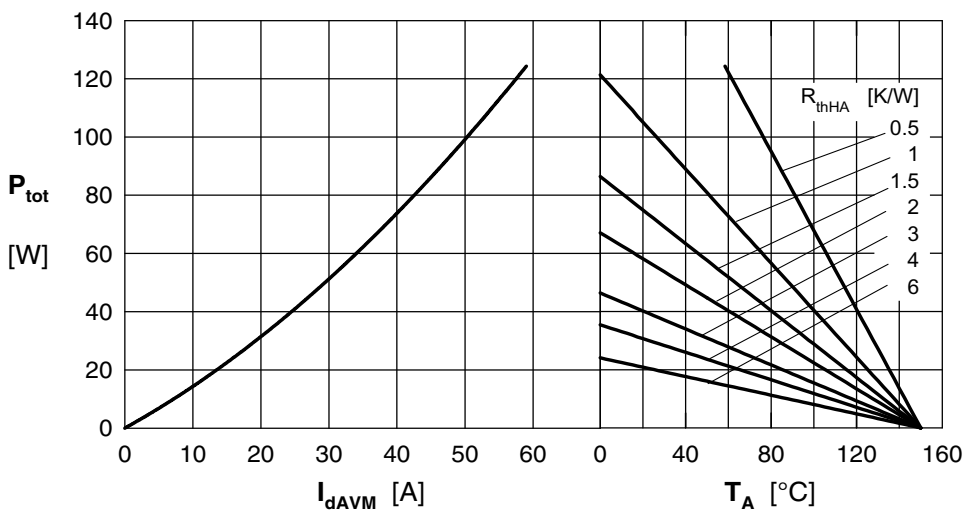


Fig. 5 Power dissipation vs. direct output current & ambient temperature (Rectifier bridge)

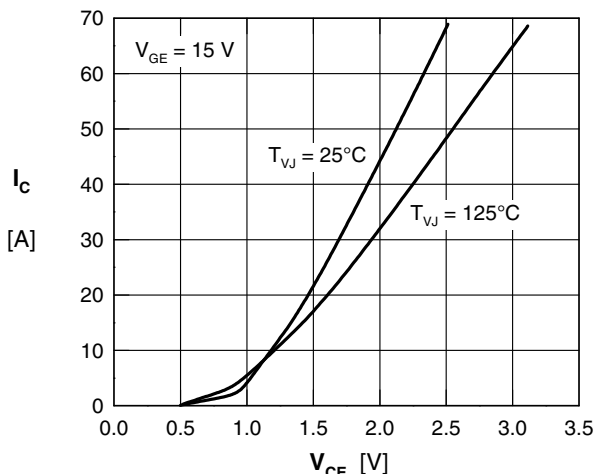


Fig. 6 IGBT, typ. output characteristics

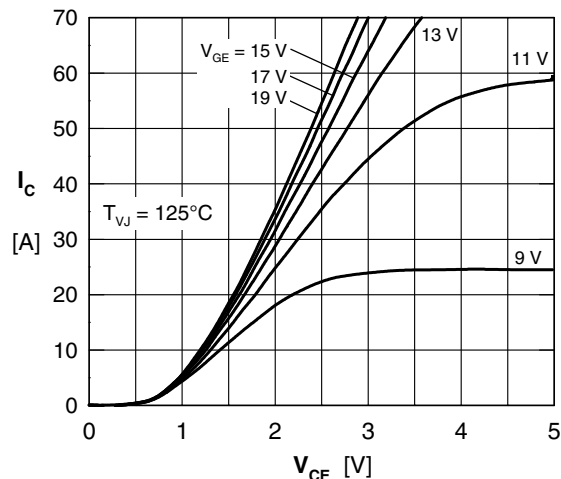


Fig. 7 IGBT, typ. output characteristics

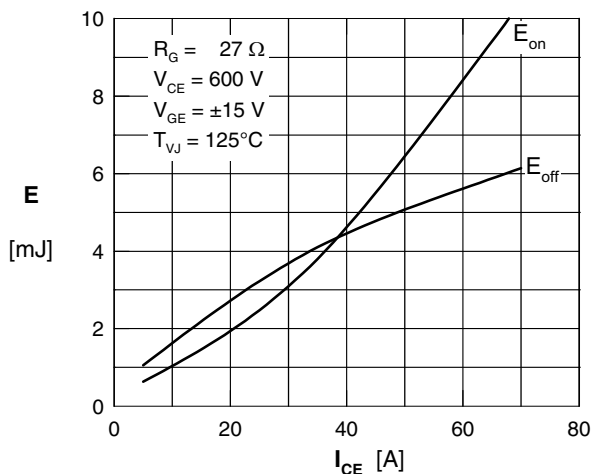


Fig. 8 IGBT, typ. switching energy versus collector current

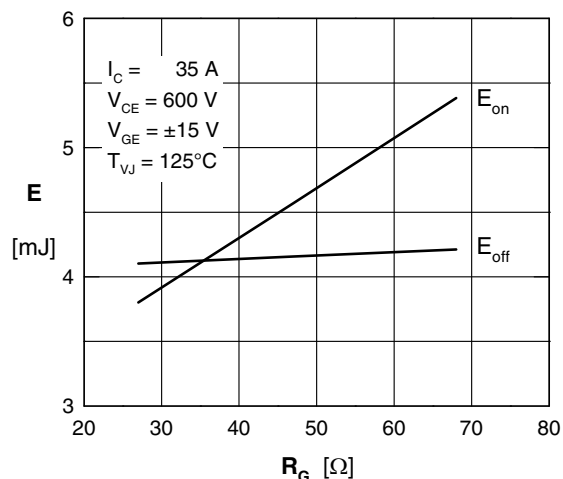


Fig. 9 IGBT, typ. switching energy versus gate resistance

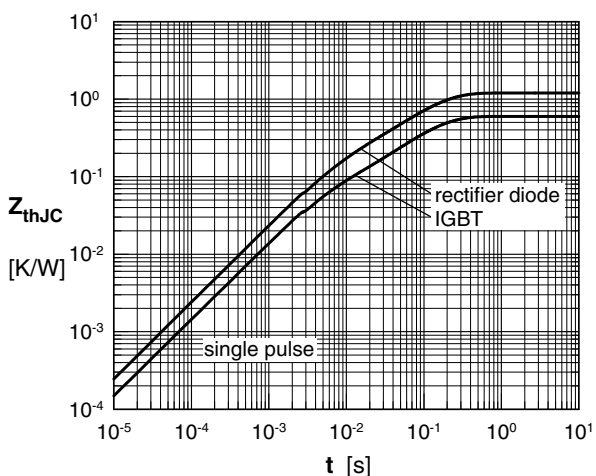


Fig. 10 Typ. transient thermal impedance

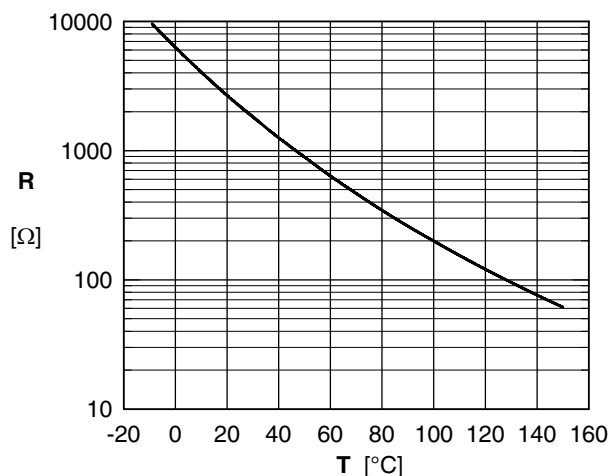


Fig. 11 Typ. thermistor resistance vs. temperature